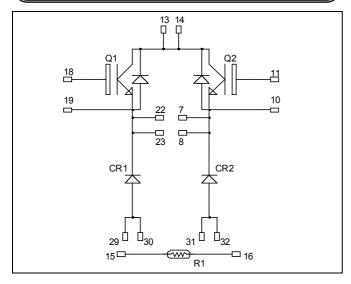
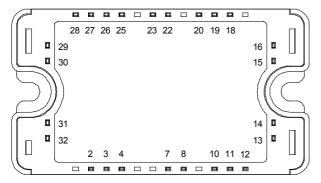


Dual Buck chopper Trench + Field Stop IGBT3 Power Module





All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

$V_{CES} = 600V$ $I_{C} = 75A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability.
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
ī	Continuous Collector Current	$T_C = 25^{\circ}C$	100	
I_{C}	Continuous Conector Current	$T_C = 80^{\circ}C$	75	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	250	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150$ °C	150A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	V
$V_{CE(sat)}$		$I_C = 75A$ $T_j = 1$	$T_{j} = 150^{\circ}C$		1.7		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_{C} = 600 \mu A$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	=0V			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			4620		_
Coes	Output Capacitance	$V_{CE} = 25V$			300		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			140		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{GE} = 300V$			110		
T _r	Rise Time				45		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 75A$			200		ns
T_{f}	Fall Time	$R_G = 4.7\Omega$			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch $V_{GE} = \pm 15V$	ning (150°C)		120		
$T_{\rm r}$	Rise Time	$V_{\text{Bus}} = 300\text{V}$			50		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75A$			250		
$T_{\rm f}$	Fall Time	$R_G = 4.7\Omega$			60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.35		mJ
Lon	Turn-on Switching Elicigy	$V_{\text{Bus}} = 300 \text{V}$	$T_j = 150$ °C		0.6		1113
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_C = 75A$ $R_G = 4.7\Omega$	$T_j = 25$ °C $T_i = 150$ °C		2.2		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V	
T	Maximum Reverse Leakage Current	$V_R=600V$	$T_j = 25^{\circ}C$			250	۸	
I_{RM}	Waximum Reverse Leakage Current	* R 000 *	v _R -000 v	$T_{j} = 150^{\circ}C$			500	μA
I_{F}	DC Forward current		Tc = 80°C		75		A	
V_{F}	Diode Forward Voltage	$I_F = 75A$	$T_i = 25^{\circ}C$		1.6	2		
* F	Blode I of ward Voluge	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		V	
t _{rr}	Reverse Recovery Time	$V_{GE} = 0V \qquad T_{j} = T_{j} = T_{j}$	$T_j = 25^{\circ}C$		100		ns	
·rr	Reverse Recovery Time	1 - 75 A	$T_{j} = 150^{\circ}C$		150		113	
0	Dayarga Dagayary Chargo	$I_F = 75A$ $V_R = 300V$	$T_j = 25^{\circ}C$		3.6		C	
Q_{rr}	Reverse Recovery Charge	$di/dt = 2000A/\mu s$	$T_{j} = 150^{\circ}C$	150°C 7.6	7.6		μС	
Б	Davarca Dagayary Engray		$T_j = 25$ °C		0.85		mJ	
$\mathrm{E_{r}}$	Reverse Recovery Energy		$T_j = 150$ °C		1.8		1113	



 $Temperature\ sensor\ NTC\ (\text{see application note APT0406 on www.microsemi.com for more information}).$

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

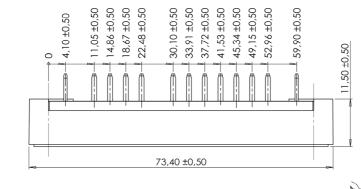
$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

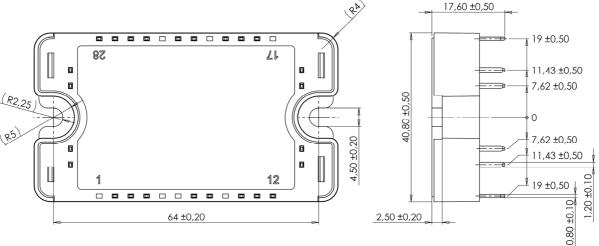
$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.60	°C/W
TthJC			Diode			0.98	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range Operating Case Temperature			-40		125	°C
$T_{\rm C}$				-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

SP3 Package outline (dimensions in mm)

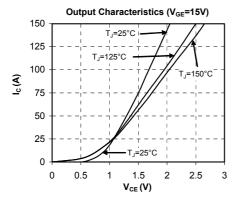


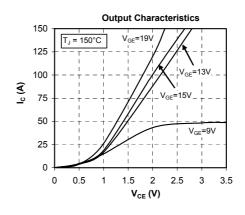


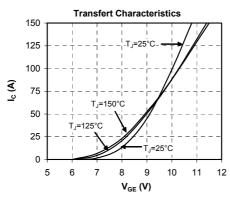
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

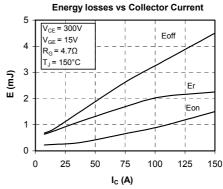


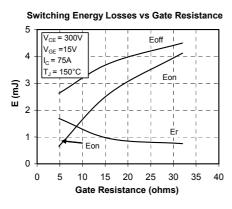
Typical Performance Curve

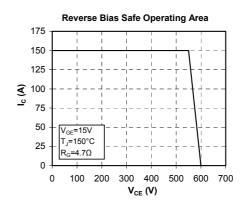


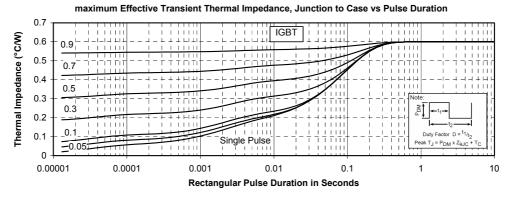




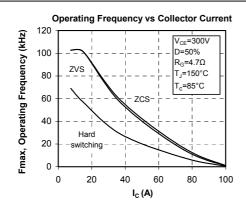


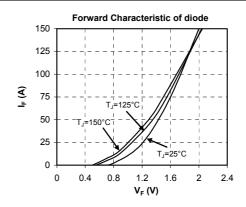


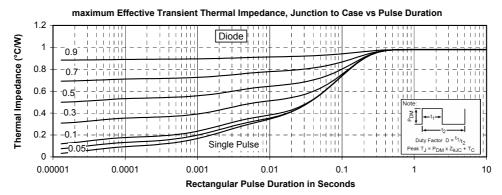












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